

General Description

The HSU10N10 is the highest performance SGT N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The HSU10N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

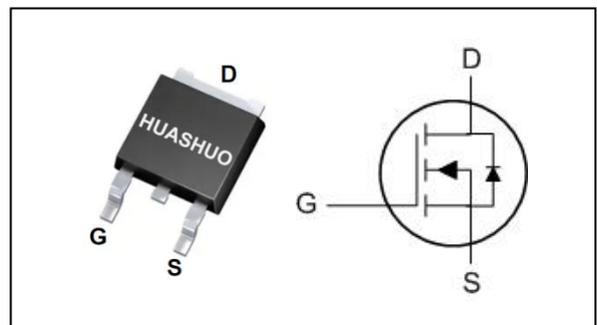
Features

- Super Low Gate Charge
- Green Device Available
- Excellent Cdv/dt effect decline
- Optimized for fast-switching application

Product Summary

V _{DS}	100	V
R _{DS(ON),TYP}	100	mΩ
I _D	10	A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	10	A
I _D @T _C =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	8	A
I _{DM}	Pulsed Drain Current ²	30	A
P _D @T _C =25°C	Total Power Dissipation ³	50	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	62	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	3.6	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	---	100	120	mΩ
		V _{GS} =4.5V, I _D =3A	---	130	165	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.7	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.1	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =2A	---	6.4	---	nC
Q _{gs}	Gate-Source Charge		---	1.1	---	
Q _{gd}	Gate-Drain Charge		---	0.99	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3Ω I _D =2A	---	1.5	---	ns
T _r	Rise Time		---	5.3	---	
T _{d(off)}	Turn-Off Delay Time		---	20	---	
T _f	Fall Time		---	15	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	310	---	pF
C _{oss}	Output Capacitance		---	20	---	
C _{rss}	Reverse Transfer Capacitance		---	3.7	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	10	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =2A, di/dt=100A/μs, T _J =25°C	---	18	---	nS
Q _{rr}	Reverse Recovery Charge		---	48	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The power dissipation is limited by 150°C junction temperature
4. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

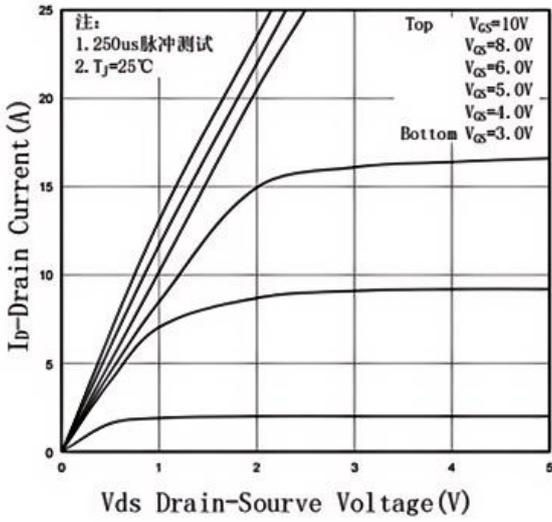


Fig.1 Output Characteristic

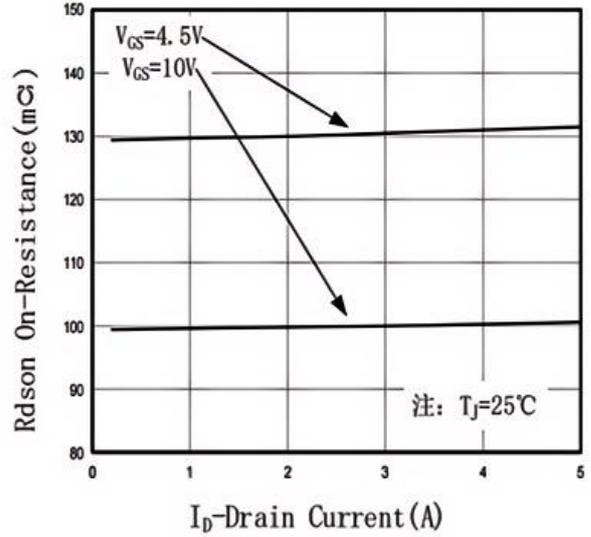


Fig.2 On-Resistance vs. Drain Current

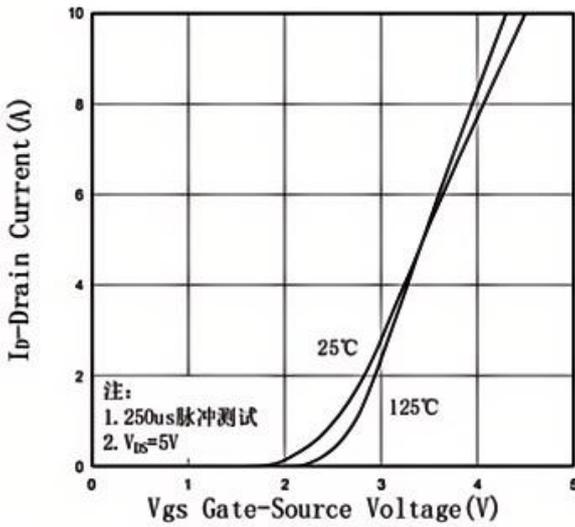


Fig.3 Transfer Characteristic

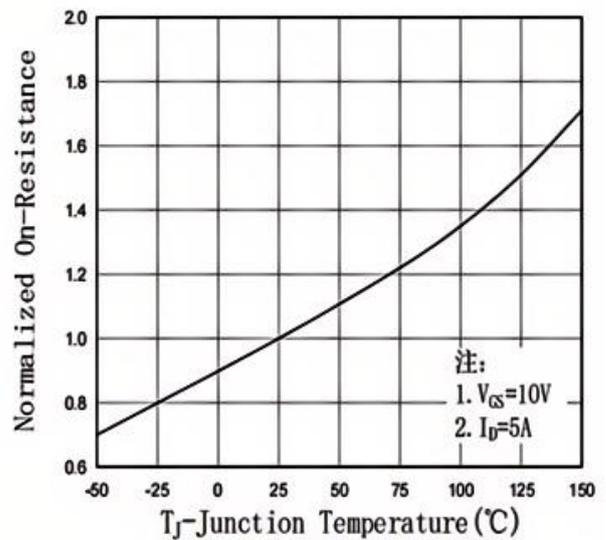


Fig.4 On-Resistance vs. Junction Temperature

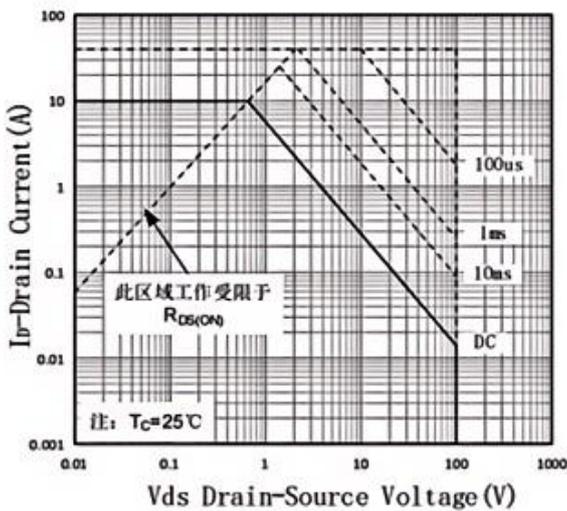


Fig.5 Safe Operation Area

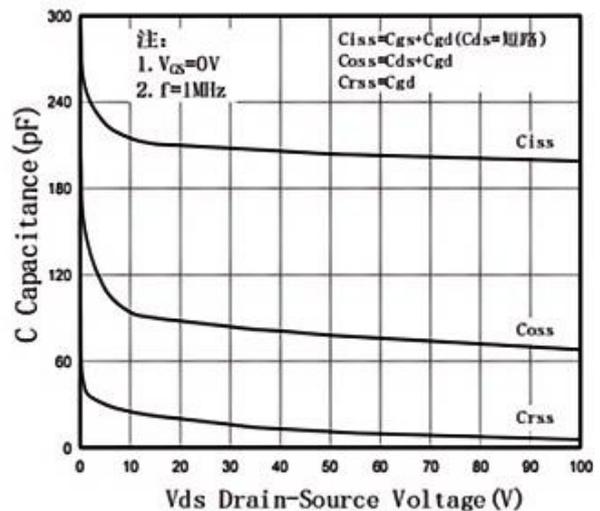


Fig.6 Capacitance Characteristic

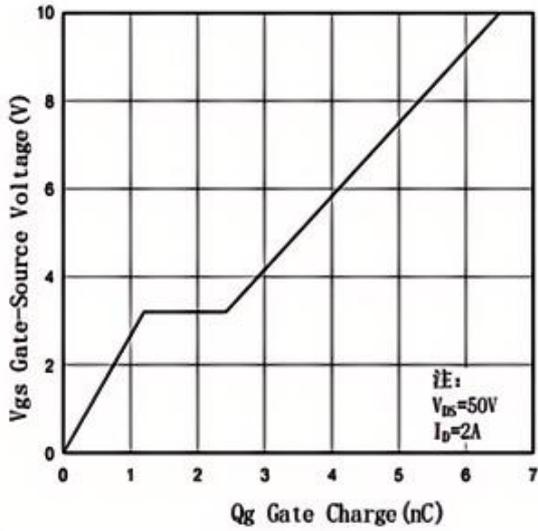


Fig.7 Gate-Charge Characteristic

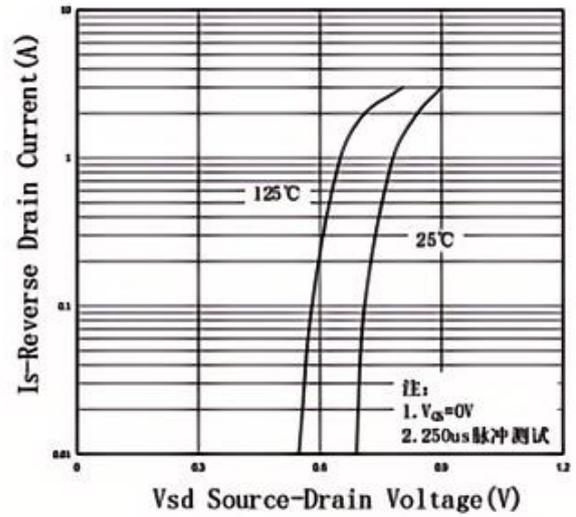


Fig.8 Body Diode Characteristic

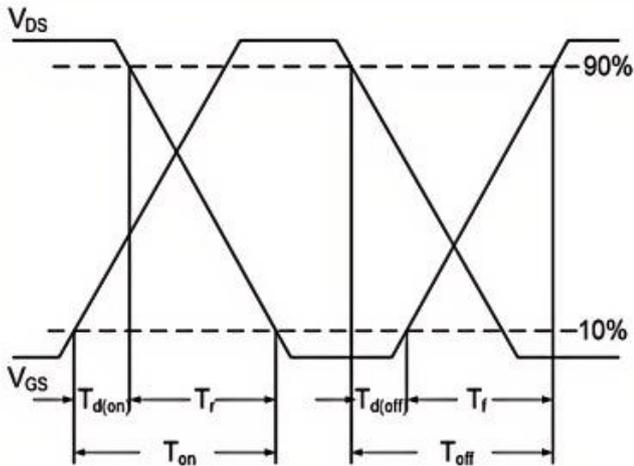


Fig.9 Switching Time Waveform

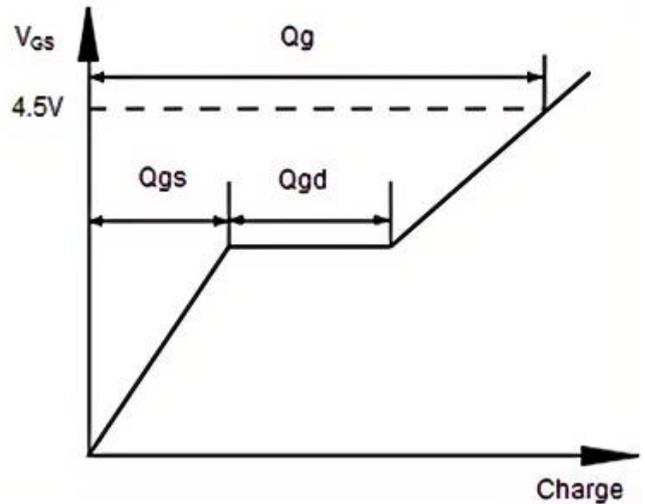


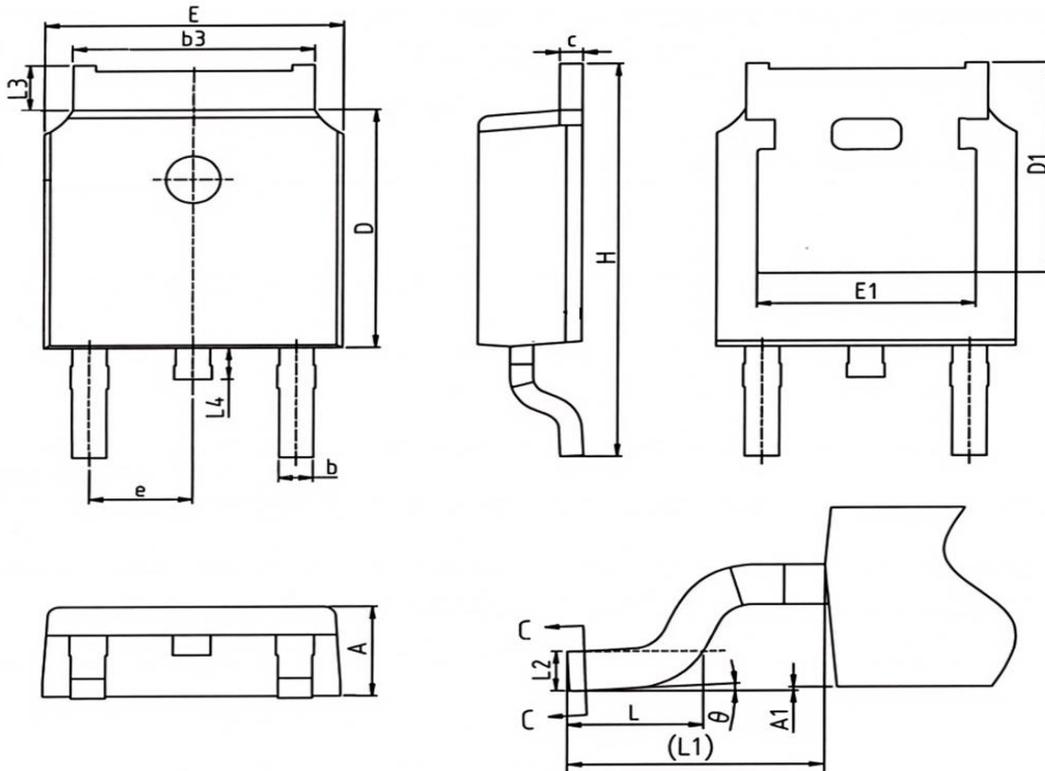
Fig.10 Gate Charge Waveform



Ordering Information

Part Number	Package code	Packaging
HSU10N10	TO-252	2500/Tape&Reel

TO252 Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
C	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	---	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°



HSU10N10 Marking:

